Dual P-Channel 1.8-V (G-S) MOSFET

CHARACTERISTICS

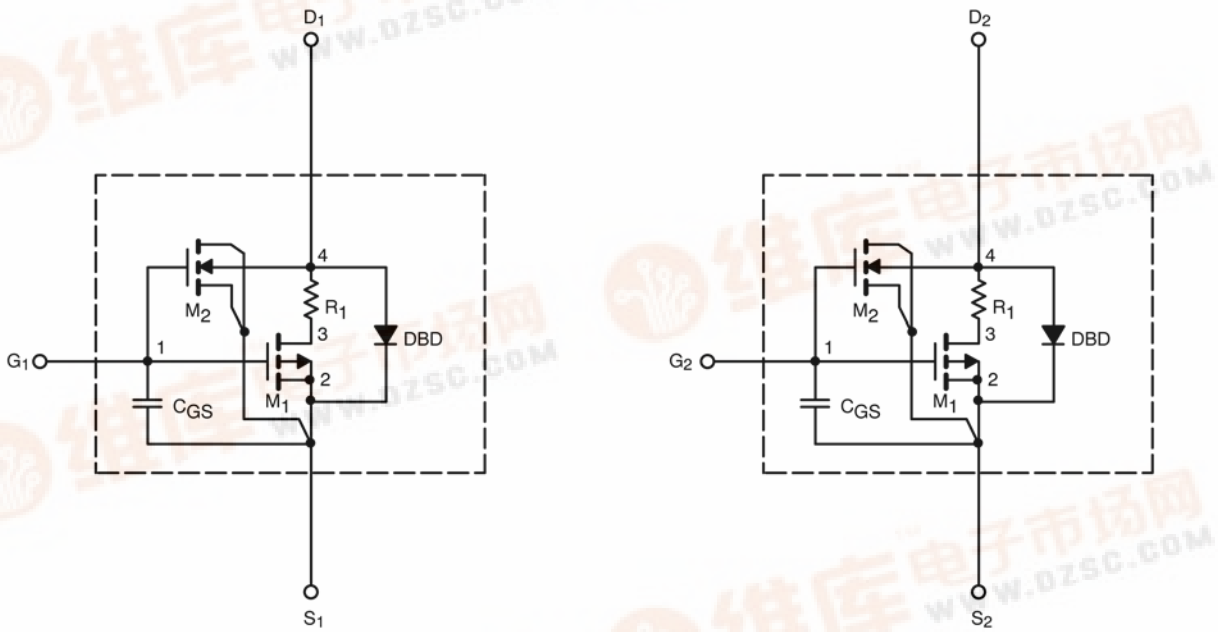
- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the –55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the –55 to 125°C temperature ranges under the pulsed 0-V to 5-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

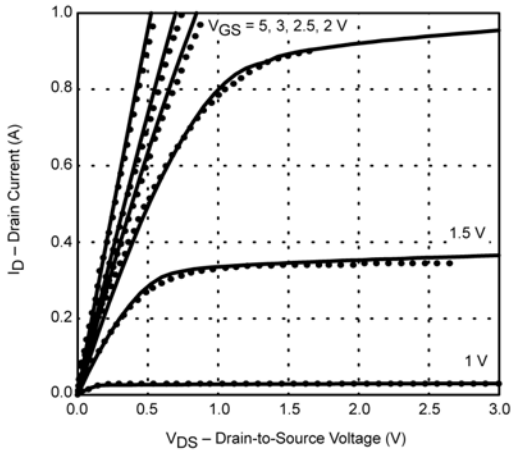
SUBCIRCUIT MODEL SCHEMATIC

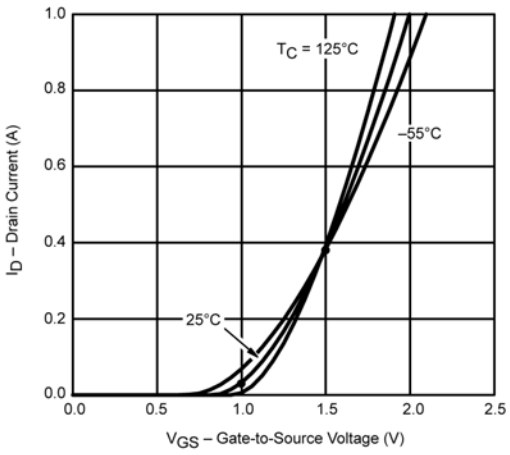


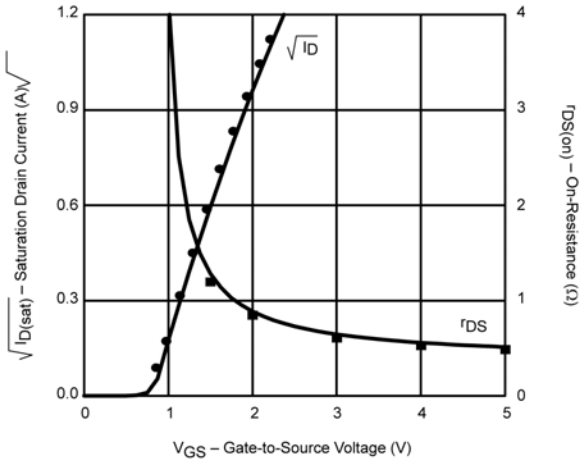
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)					
Parameter	**Symbol**	**Test Condition**	**Simulated Data**	**Measured Data**	**Unit**
Static					
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = –250 μA	0.78		V
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = –5 V, V_{GS} = –4.5 V	5.8		A
Drain-Source On-State Resistance [a]	$r_{DS(on)}$	V_{GS} = –4.5 V, I_D = –0.53 A	0.54	0.57	Ω
		V_{GS} = –2.5 V, I_D = –0.44 A	0.77	0.80	
		V_{GS} = –1.8 V, I_D = –0.20 A	1.05	1.25	
Forward Transconductance [a]	g_{fs}	V_{DS} = –10 V, I_D = –0.53 A	1.19	1.1	S
Diode Forward Voltage [a]	V_{SD}	I_S = –0.23 A, V_{GS} = 0 V	–0.76	–0.80	V
Dynamic [b]					
Total Gate Charge	Q_g	V_{DS} = –6 V, V_{GS} = –4.5 V, I_D = –0.53 A	0.72	1.5	nC
Gate-Source Charge	Q_{gs}		0.14	0.40	
Gate-Drain Charge	Q_{gd}		0.12	0.25	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = –6 V, R_L = 12 Ω I_D ≅ –0.50 A, V_{GEN} = –4.5 V, R_G = 6 Ω	6	6	ns
Rise Time	t_r		7	20	
Turn-Off Delay Time	$t_{d(off)}$		23	10	
Fall Time	t_f		7	10	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = –0.23 A, di/dt = 100 μs	15	20	

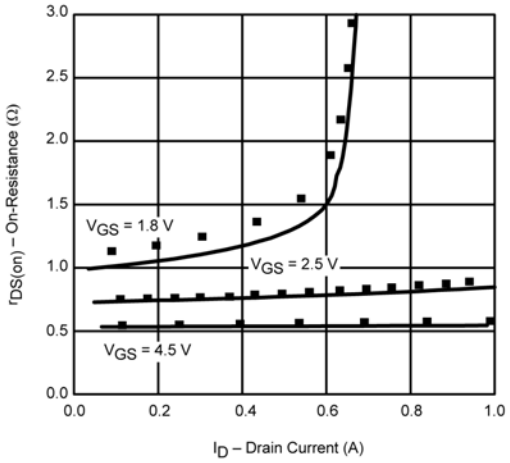
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

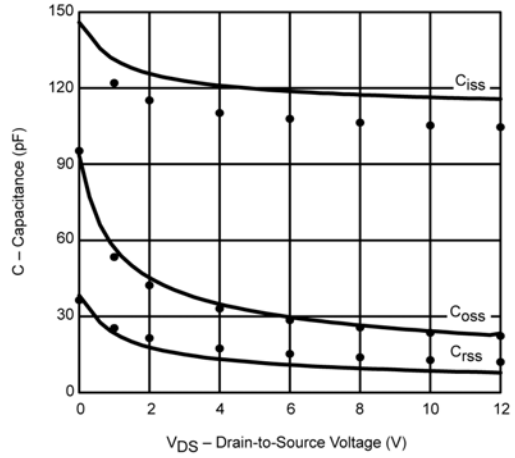
COMPARISON OF MODEL WITH MEASURED DATA (T_J=25°C UNLESS OTHERWISE NOTED)

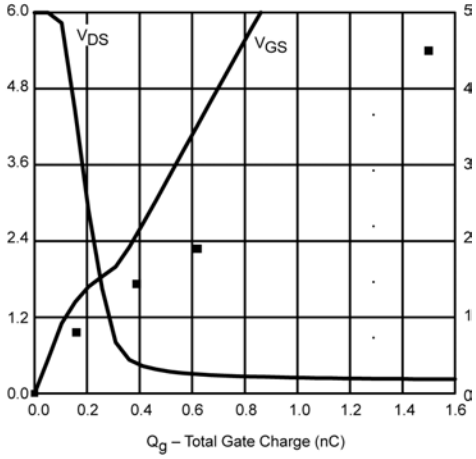












Note: Dots and squares represent measured data.